International
IOR Rectifier

Preliminary Data Sheet PD - 9.1029A

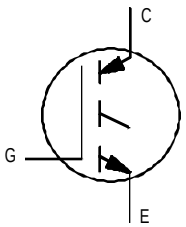
IRGPH40M

INSULATED GATE BIPOLAR TRANSISTOR

Short Circuit Rated
Fast IGBT

Features

- Short circuit rated - 10µs @ 125°C, V_{GE} = 15V
- Switching-loss rating includes all "tail" losses
- Optimized for medium operating frequency (1 to 10kHz)



n-channel

V_{CES} = 1200V

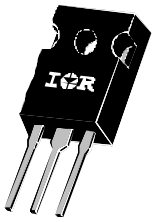
$V_{CE(sat)} \leq$ 3.4V

@V_{GE} = 15V, I_C = 18A

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.



TO-247AC

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
I_C @ T_C = 25°C	Continuous Collector Current	31	A
I_C @ T_C = 100°C	Continuous Collector Current	18	
I_{CM}	Pulsed Collector Current ①	62	
I_{LM}	Clamped Inductive Load Current ②	62	
t_{sc}	Short Circuit Withstand Time	10	µs
V_{GE}	Gate-to-Emitter Voltage	±20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	15	mJ
P_D @ T_C = 25°C	Maximum Power Dissipation	160	W
P_D @ T_C = 100°C	Maximum Power Dissipation	65	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	------	------	0.77	°C/W
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	------	0.24	------	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	------	------	40	
Wt	Weight	------	6 (0.21)	------	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	----	----	V	V_{GE} = 0V, I_C = 250µA
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	20	----	----	V	V_{GE} = 0V, I_C = 1.0A
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	----	1.1	----	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	----	2.3	3.4	V	I_C = 18A
		----	3.0	----		I_C = 31A V_{GE} = 15V
		----	2.8	----		I_C = 18A, T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	----	5.5		V_{CE} = V_{GE}, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	----	-14	----	mV/°C	V_{CE} = V_{GE}, I_C = 250µA
g_{fe}	Forward Transconductance ⑤	4.0	10	----	S	V_{CE} = 100V, I_C = 18A
I_{CES}	Zero Gate Voltage Collector Current	----	----	250	µA	V_{GE} = 0V, V_{CE} = 1200V
		----	----	3500		V_{GE} = 0V, V_{CE} = 1200V, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	----	----	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	----	50	75	nC	I_C = 18A
Q_{ge}	Gate - Emitter Charge (turn-on)	----	11	21		V_{CC} = 400V
Q_{gc}	Gate - Collector Charge (turn-on)	----	15	30		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	----	30	----	ns	T_J = 25°C
t_r	Rise Time	----	21	----		I_C = 18A, V_{CC} = 960V
$t_{d(off)}$	Turn-Off Delay Time	----	400	890		V_{GE} = 15V, R_G = 10Ω
t_f	Fall Time	----	390	740		Energy losses include "tail"
E_{on}	Turn-On Switching Loss	----	1.1	----	mJ	
E_{off}	Turn-Off Switching Loss	----	4.0	----		
E_{ts}	Total Switching Loss	----	5.1	8.0		
t_{sc}	Short Circuit Withstand Time	10	----	----	µs	V_{CC} = 720V, T_J = 125°C
						V_{GE} = 15V, R_G = 10Ω, V_{CPK} < 1000V
$t_{d(on)}$	Turn-On Delay Time	----	28	----	ns	T_J = 150°C,
t_r	Rise Time	----	24	----		I_C = 18A, V_{CC} = 960V
$t_{d(off)}$	Turn-Off Delay Time	----	600	----		V_{GE} = 15V, R_G = 10Ω
t_f	Fall Time	----	870	----		Energy losses include "tail"
E_{ts}	Total Switching Loss	----	9.0	----	mJ	
L_E	Internal Emitter Inductance	----	13	----	nH	Measured 5mm from package
C_{ies}	Input Capacitance	----	1360	----	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	----	100	----		V_{CC} = 30V
C_{res}	Reverse Transfer Capacitance	----	15	----		f = 1.0MHz

Notes:

① Repetitive rating; V_{GE}=20V, pulse width limited by max. junction temperature.

② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G= 10Ω

③ Repetitive rating; pulse width limited by maximum junction temperature.

④ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

⑤ Pulse width 5.0µs, single shot.

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/